



Power Aware Features of IBISv5.0 – Accuracy and Challenges

Vipul Pursottam Patel

Prabhat Ranjan

Richa Ahuja

- ST Microelectronics

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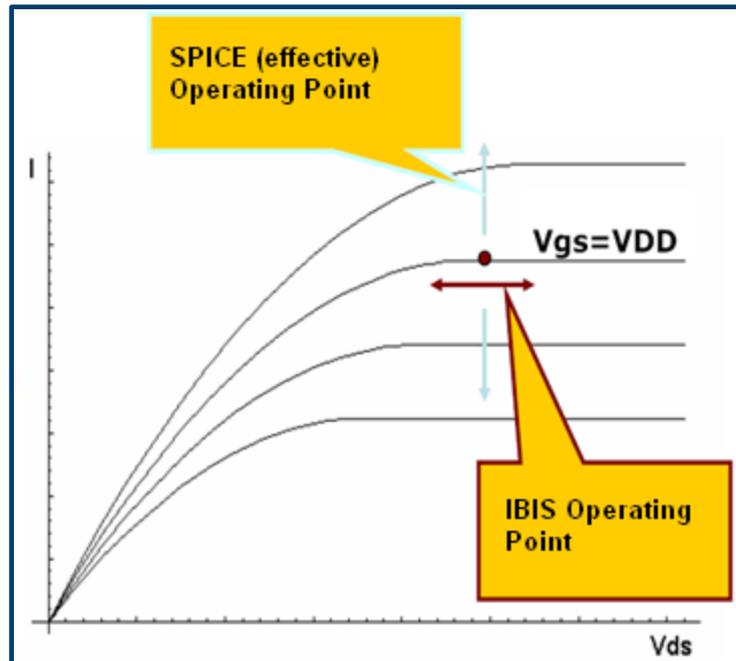
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- Introduction
- BIRD98 [ISSO PU] / [ISSO PD]
- BIRD95 [Composite Current]
- Accuracy Enhancements
- Challenges

- For Improved SSO simulations in non-ideal power supply environment IBIS ver.5.0 introduced the following features :
 - Added **[ISSO PU] & [ISSO PD]** tables proposed in BIRD98.
 - To model Gate Modulation effect.
 - Added **[Composite Current]** tables proposed in BIRD95.
 - For more accurate analysis for ground and power bounce associated with simultaneous switching noise.

- Due to SSO noise, the actual drive strength may vary during transients depending on the instantaneous value of the supply voltage.

- This phenomena is usually called the “**Gate Modulation Effect**”



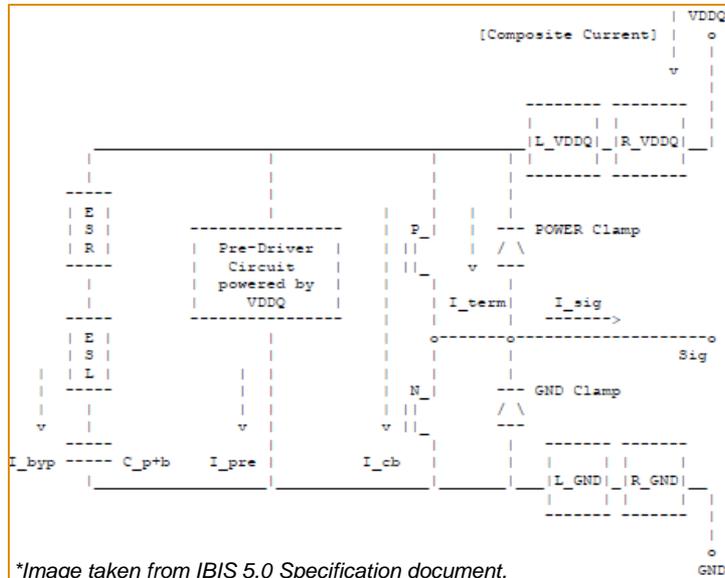
- In IBIS (prior to IBISv5) Working point can move only along the same **Vgs = VDD** characteristic.
- During supply bounce, actual working point shifts to **Vgs = VDD ± ΔV_{bounce}** characteristics.
- Higher is the bouncing noise, the higher is the mismatching between IBIS and Spice results.

- [ISSO PU] / [ISSO PD]** define the effective current of the pullup/pulldown structures as a function of the voltage on the pullup/pulldown reference nodes.

BIRD95 [Composite Current]



- The current causing the Supply bounce will include :
 - I_{byp} - Bypass current
 - I_{pre} - Pre-Driver current
 - I_{cb} - Crow-bar current
 - I_{term} - Termination current (if Present)



- I_{byp} & I_{pre} play a significant role in determining the supply bounce.
- Not modeled by IBIS ver. Prior to 5.0

$$I_{total} = "I_{byp}" + "I_{pre}" + "I_{cb}" + "I_{term}"$$

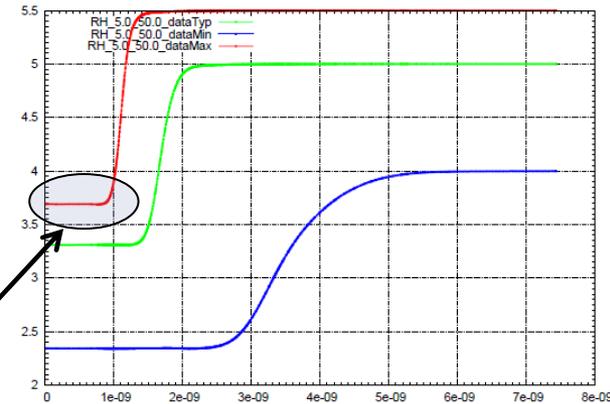
([Composite Current])

- Describes **Rising** and **Falling** edge total current from the **Power Reference** terminal of the buffer.

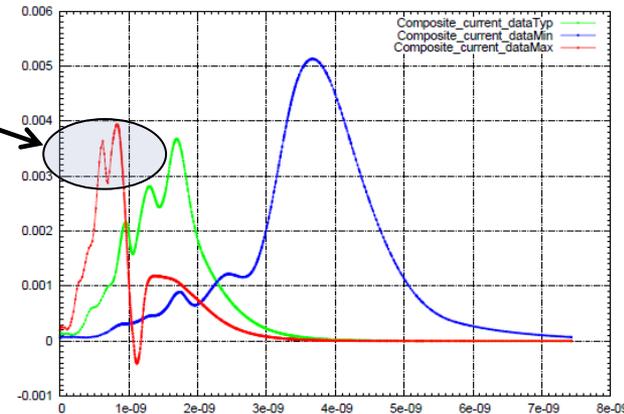
[Composite Current] Observation 1



- “The currents documented in the I-T table correspond to the voltages in the V-T table at the identical time points and for the given *_fixture load.” *
- The best data points for a specific V-T table will not be the same best points for corresponding I-T table .
- Generation tools can miss Important information in I-T data.



Pre-driver current peaks occur in the region of initial constant voltage.



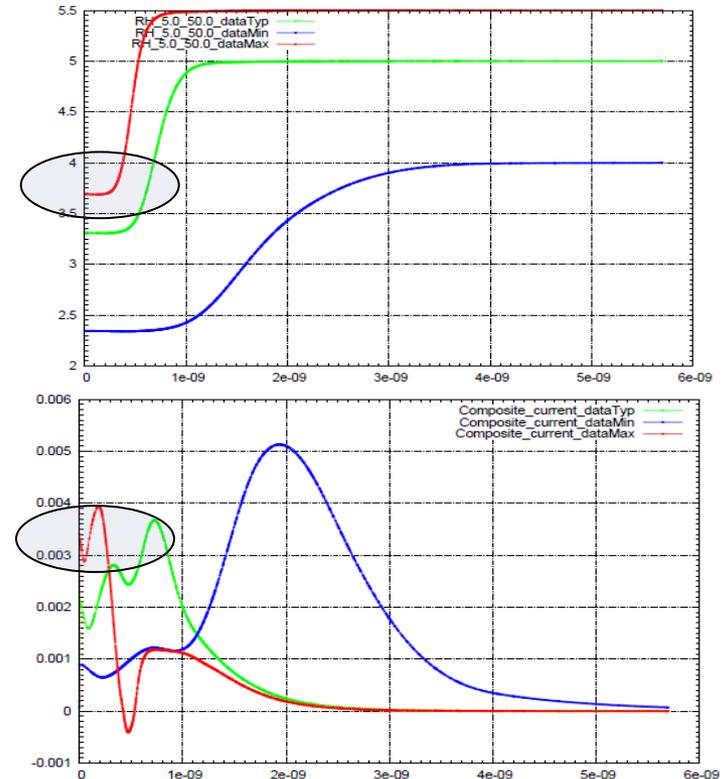
*Text taken from IBIS 5.0 Specification document.

[Composite Current] Observation 2



- For High Speed buffers, Some simulators require removal of Initial dead time (if greater than half bit period of the driving signal), to avoid overclocking.
 - If Initial dead time removed from V-T tables , I-T waveforms also need to be adjusted similarly.
 - Pre-driver current information will be lost.
 - [Composite Current] information cannot be effectively used.
 - Model developers need to support 2 Separate Models, one with dead time removed and other without removal.

This constraint (**I-T data time-correlated with V-T data**) need to be removed to accurately model the V-T Waveforms and I-T waveform. (“BIRD 141”)



[Composite Current] Observation 3



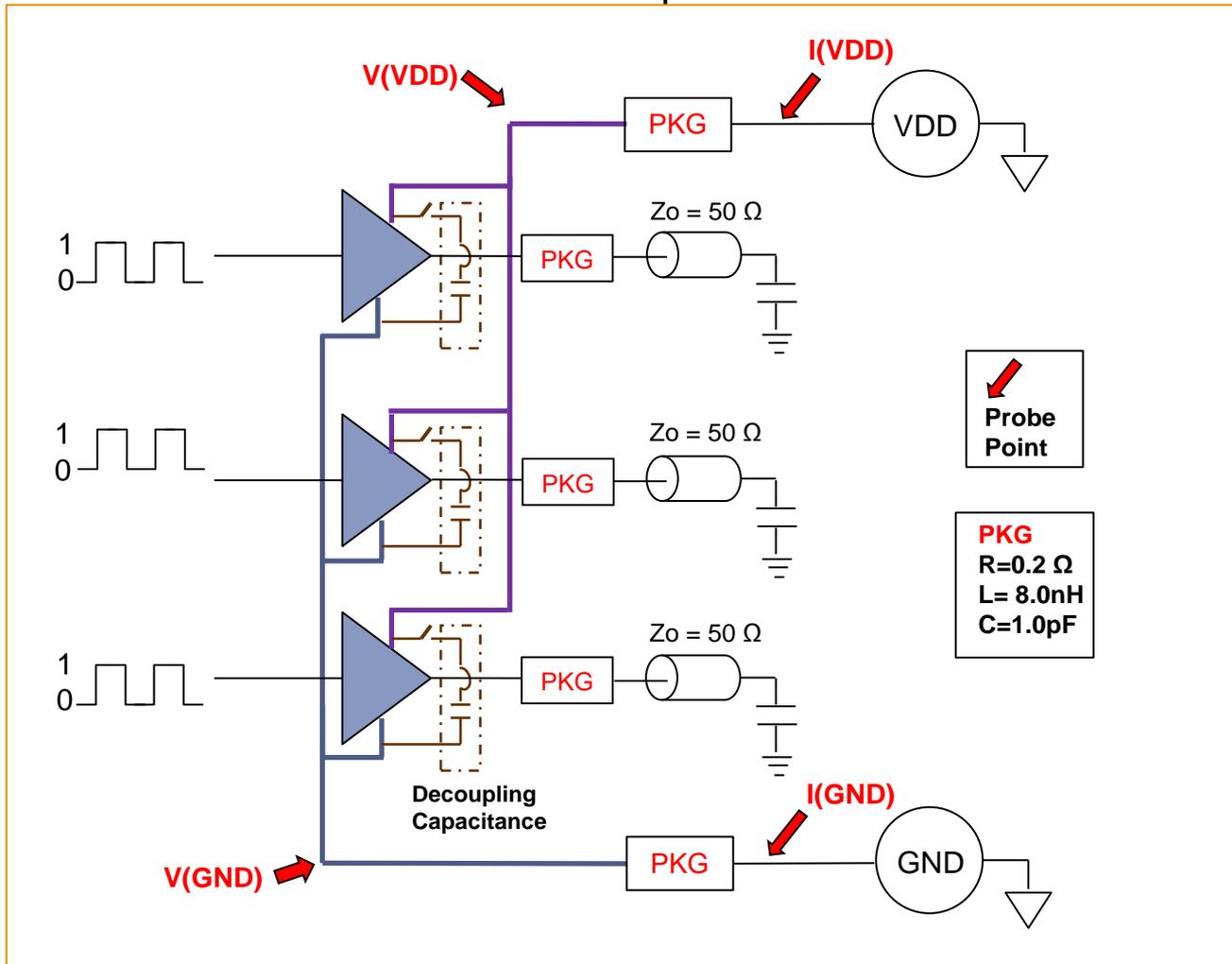
- **No info regarding Pull Down reference terminal current in IBIS models !!**
 - *Simulators can only assume Pull Down terminal current equal to Pull Up reference current ?*
 - *Accuracy of Power Down terminal current simulations reduced.*
 - *May impact SSN number estimation.*

Accuracy Enhancements

Simulation Setup

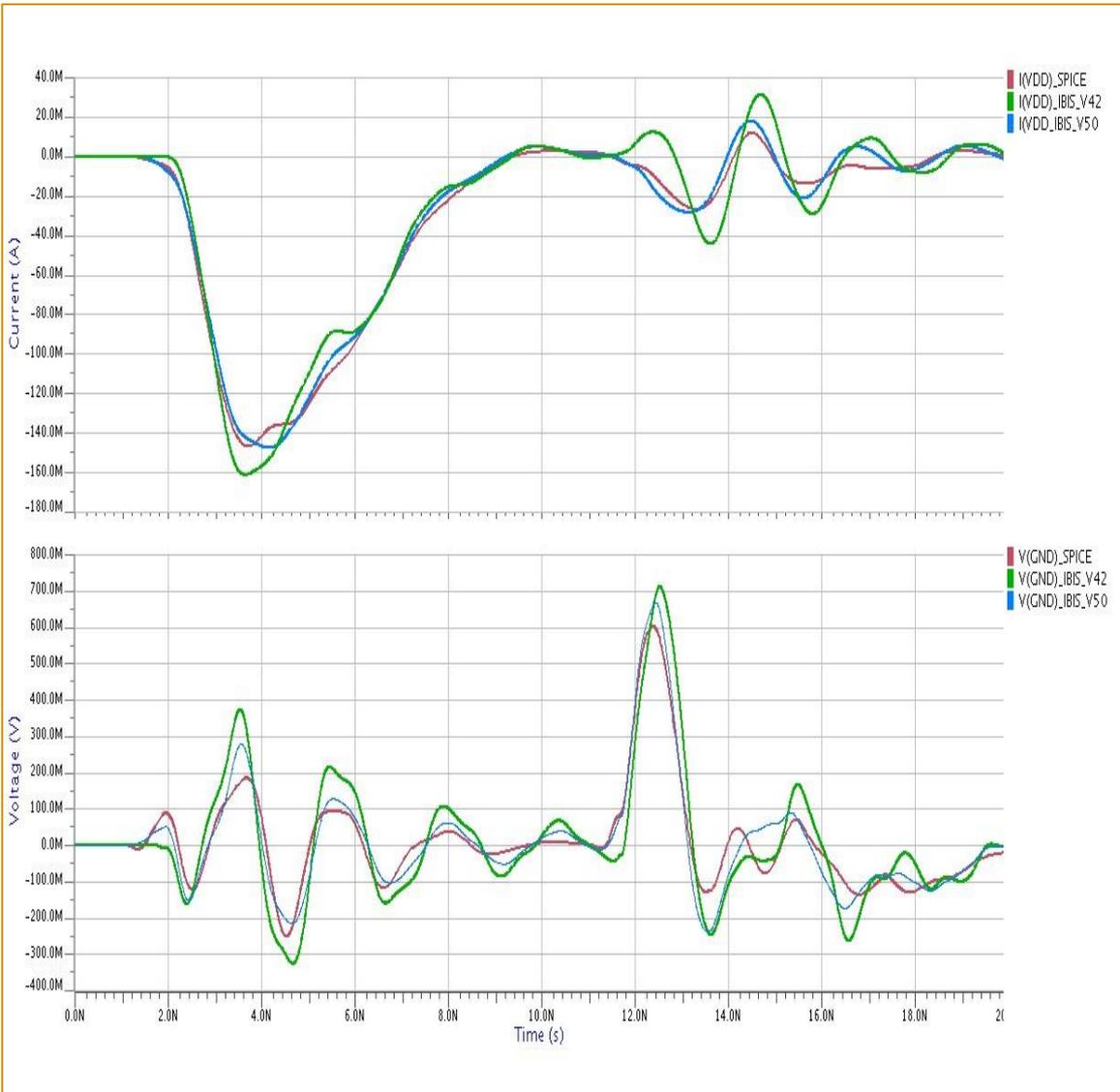


- Comparison of power/ground supply node current and voltage for IBIS 4.2 and IBIS 5.0 model with Reference Spice model in SSO simulation.



- Corner : Max.
- Frequency : 50MHz
- Far End Capacitive Load: 25pF
- Decoupling Capacitance between Supply and ground of each Buffer: 4pF

Result 1 : I(VDD)/V(GND) SPICE-IBISv4.2-IBISv5.0



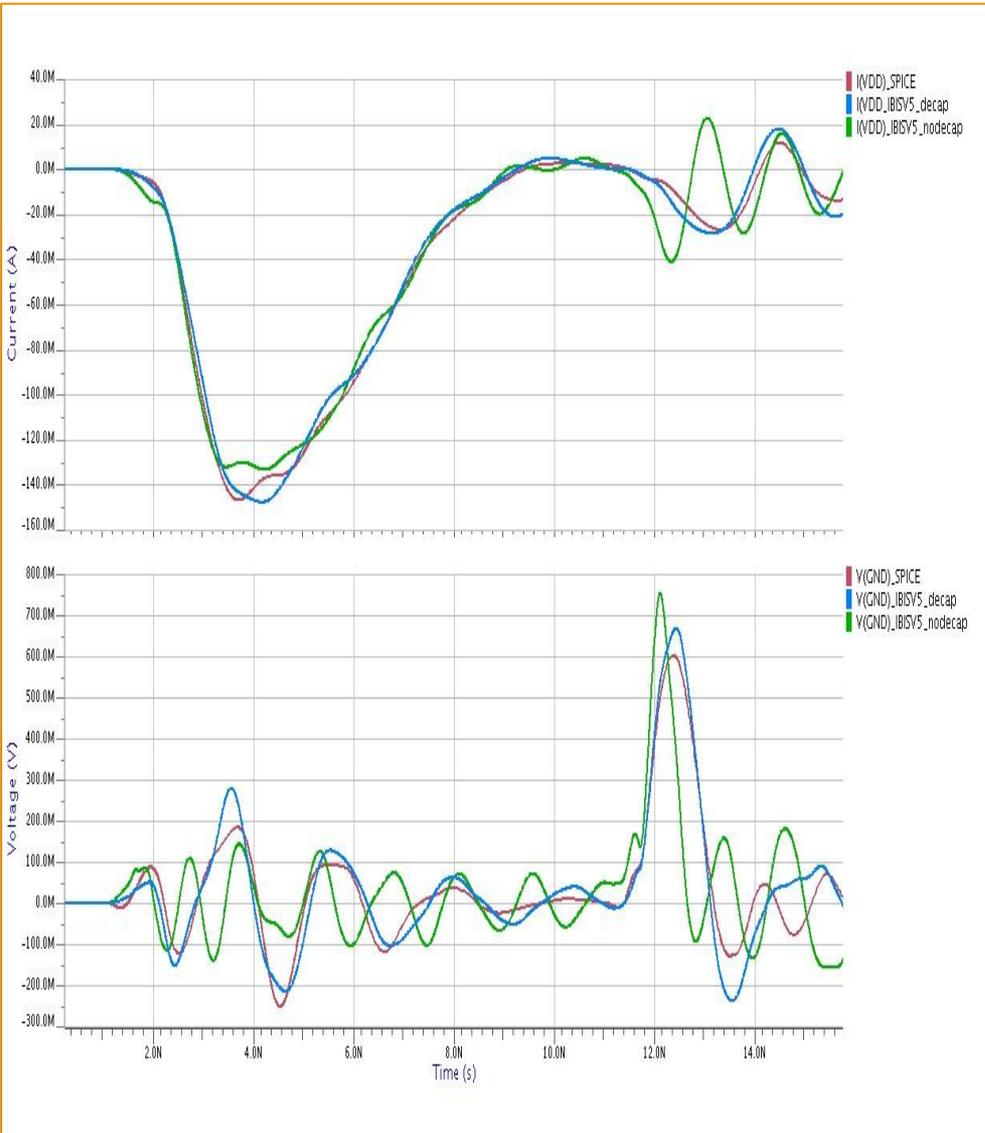
- Improved matching In **Power supply current** Simulation.
- Improved matching In **Supply bounce** Simulation

Accuracy Enhanced of IBIS Models With :

***[Composite Current],
[ISSO PU],
[ISSO PD].***

* From SPICE simulation

Result 2 : I(VDD)/V(GND) SPICE-IBISv5.0 (with & without decoupling capacitance)



- Improved matching with de-cap added to spice model in **Power supply current** Simulation.
- Improved matching with de-cap added to spice model in **Ground bounce** Simulation.

No method to specify 'individual buffers internal De-coupling capacitance' between its supply nodes in IBIS syntax.

* From SPICE simulation

- **[Composite Current]** time-correlation with V-T waveforms can lead to loss of important pre-driver current info in overclocking and non-overclocking models. This constraint need to be removed.
- No method to specify **‘individual buffers internal De-coupling capacitance’** between its supply nodes in IBIS syntax
 - *Can specify On-die decoupling capacitance between pins using Series Model at component level.*
 - *As a model supplier, Internal de-coupling capacitance is required during validations as well as to pass on this info to customers for simulations at their end.*

THANK YOU